

# WANT TO BOOST EFFICIENCY IN YOUR DC-DC CONVERTER?

## CHANGE YOUR MOSFET, NOT YOUR DESIGN.

STMicroelectronics STripFET™ III devices, with world beating ON-resistance \* gate charge figure of merit results, are the benchmark FET for DC-DC converters including buck topologies, and their derivatives, widely used in computer and telecom applications. Gate charge for the high-side *control*FET is significantly reduced as is ON-resistance for the low-side *synchronous* FET.

But that's not all. Reverse recovery characteristics of the synchronous FET parasitic body diode have been optimized, while the very low intrinsic gate resistance of STripFET III devices plays a key role in reducing switching losses at higher frequencies.

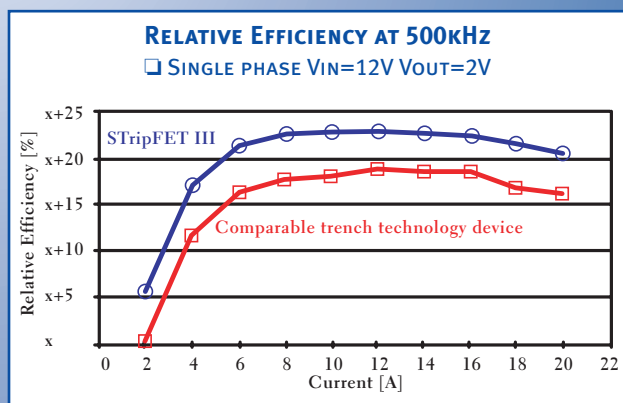
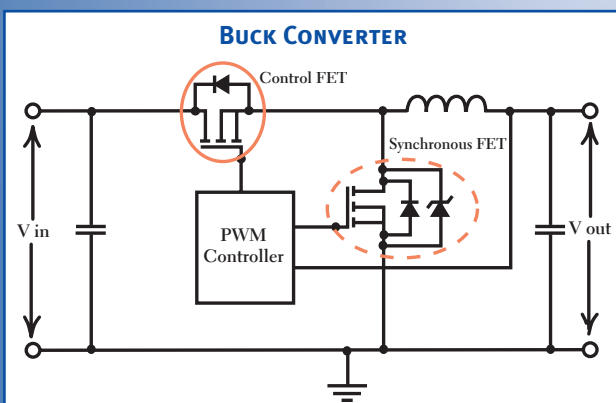
And there's more. New bondless packages, ClipPAK™ and bondless SO-8, further improve thermal performance and reduce conduction losses giving STripFET III even better figure of merit results.

Control FET					
Type	$V_{(BR)DSS}$ [V]	$I_D$ [A]	$R_{DS(on)max}$ @10V [mΩ]	$Q_g$ (typ.) @10V [nC]	Package
STS12NH3LL	30	12	14*	9.5*	SO-8
STD38NH02L	20	38	13.5	18	DPAK
STB50NH02L	20	50	13.5	18	D <sup>2</sup> PAK
STD50NH02L	20	50	10	22	DPAK

\*Available in Q1 2003. Values refer to 4.5V VGS

Synchronous FET					
Type	$V_{(BR)DSS}$ [V]	$I_D$ [A]	$R_{DS(on)max}$ @10V [mΩ]	$Q_g$ (typ.) @10V [nC]	Package
STD90NH02L	20	60	6	47.5	DPAK
STD100NH02L	20	60	4.8	62	DPAK
STB130NH02L	20	90	4.4	69	D <sup>2</sup> PAK
STS25NH3LL	30	25	3.5	60	SO-8
STD150NH02L	20	150	3.3	69	ClipPAK <sup>(1)</sup>

(1) same footprint as DPAK



For more information on STripFET III mosfet products and technologies, go to [www.st.com/stripfet](http://www.st.com/stripfet)



Helping lead the way